(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
13 September 2007 (13.09.2007)

PCT

(10) International Publication Number
WO 2007/103610 A2

(51) International Patent Classification:
H01L 29/76 (2006.01) *H01L 21/332* (2006.01)

(21) International Application Number:
PCT/US2007/061843

(22) International Filing Date: 8 February 2007 (08.02.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/361,624 24 February 2006 (24.02.2006) US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LV, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

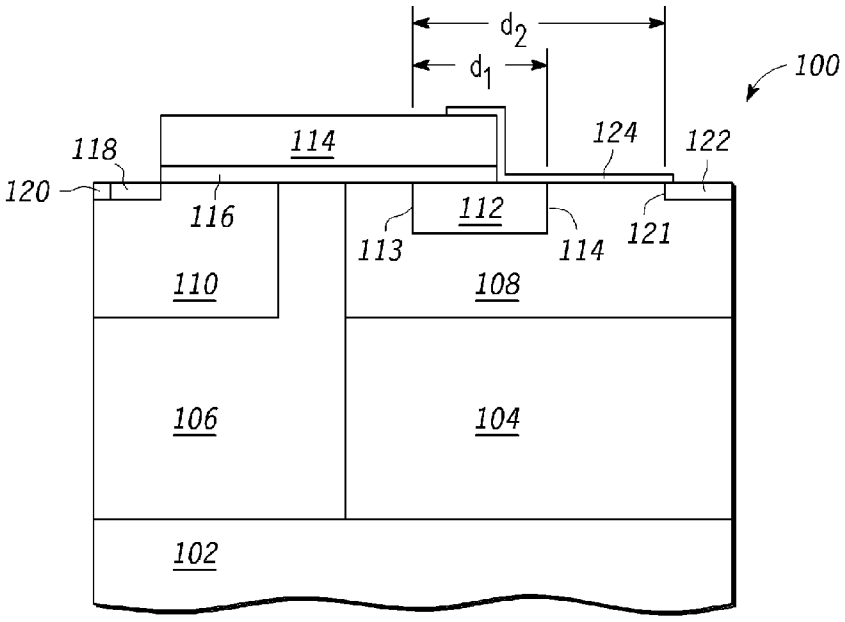
(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *without international search report and to be republished upon receipt of that report*

[Continued on next page]

(54) **Title:** METHOD AND APPARATUS FOR A STEPPED-DRIFT MOSFET



(57) **Abstract:** A power metal-oxide-semiconductor field effect transistor (MOSFET) (100) incorporates a stepped drift region including a shallow trench insulator (STI) (112) partially overlapped by the gate (114) and which extends a portion of the distance to a drain region (122). A silicide block extends from and partially overlaps STI (112) and drain region (122). The STI (112) has a width that is approximately 50% to 75% of the drift region.

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